

Focused Ion Beam/Scanning Electron Microscopy

Helios NanoLab 660

DESCRIPTION

The Helios 660 NanoLab is an exclusive dual-beam microscope for ultra-high resolution imaging, analysis and fabrication at the nanoscale. It combines a monochromated field emission scanning electron microscope (FE-SEM) with an advanced focused ion beam (FIB) column. The instrument has superb imaging capabilities, providing subnanometer resolution across the whole 1-30 kV range. It is equipped with in-lens SE and BSE detectors, a STEM detector plus EDS and EBSD analyzers. The FIB column's exceptional low-voltage performance together with the Gas Injection System (GIS) and Easy Lift nanomanipulator makes this instrument ideally suited for TEM lamella preparation and observation. The Helios Nanolab is also capable of automated 3D chemical and crystallographic analysis as well as structure reconstruction. Moreover, The CryoMAT module extension allows the investigation of many non-traditional, non-wet materials like hard/soft mixes, composites or beam sensitive materials.



APPLICATION EXAMPLES

Electron Optics		Imaging Detectors (detected signals)	Micromanipulator	
Column type	Elstar UC		Manipulator type	EasyLift EX
Source type	Schottky FEG with monochromator	TLD (SE, BSE)	Movements	X,Y,Z, rotation
		ICD (BSE)	Sample Stage	
Imaging modes	field free	MD (BSE)	Х,Ү	150 mm (piezo driven)
	XHR immersion	ETD (SE, BSE)	z	10 mm
	EDS optimized	FSD (BSE)	Rotation	360 ° continuous
	Beam deceleration	CBS (BSE)	Tilt	- 10 ° to + 60 °
Probe current	0.8 pA to 100 nA	STEM (TE)	Tilt accuracy	0.1° (50° – 54°)
Landing energy	20 eV to 30 keV	ICE (SE, SI)	Maximum Sample Sizes (incl. holder)	
Ion Optics		Analytical Detectors	Maximum size	150 mm
Column type	Tomahawk	EBSD EDAX Hikari XP	Max. thickness (loadlock)	9 mm
Source type	Ga LMIS	EDS EDAX SDD Octane Super 60 mm ²	Max. thickness via chamber door	55 mm
Probe current	0.1 pA to 65 nA	Others	Special Stage Option	
Landing energy	500 eV to 30 keV	IR camera	Stage type	CryoMAT
Resolution		Nav-Cam+	Working range	- 190 °C to + 50 °C
E beam	0.6 nm @ 30 kV (STEM)	Integrated Beam current measurement	Accessories	
	0.6 nm @ 15-2 kV		Plasma cleaner	
	0.7 nm @ 1kV	GIS	Cryo cleaner	
	1 nm @ 500 V (ICD)	carbon	Manual loadlock	
	Column type Source type Imaging modes Imaging modes Probe current Landing energy Column type Source type Probe current Landing energy Resolution	Column typeElstar UCSource typeSchottky FEG with monochromatorImaging modesfield freeXHR immersionEDS optimizedBeam decelerationBeam decelerationProbe current0.8 pA to 100 nALanding energy20 eV to 30 keVIon OpticsTomahawkSource typeGa LMISProbe current0.1 pA to 65 nALanding energy500 eV to 30 keVProbe current0.1 pA to 65 nALanding energy500 eV to 30 keVProbe current0.6 nm @ 30 kV (STEM)0.6 nm @ 15-2 kV0.7 nm @ 1kV	Column typeElstar UC(detected signals)Source typeSchottky FEG with monochromatorTLD (SE, BSE)Imaging modesfield freeMD (BSE)Imaging modesfield freeMD (BSE)XHR immersionETD (SE, BSE)EDS optimizedFSD (BSE)Beam decelerationCBS (BSE)Probe current0.8 pA to 100 nASTEM (TE)Landing energy20 eV to 30 keVICE (SE, SI)Ion OpticsAnalytical DetectorsColumn typeTomahawkEBSD EDAX Hikari XPSource typeGa LMISCDS EDAX SDD Octane Super 60 mm²Probe current0.1 pA to 65 nAOthersLanding energy500 eV to 30 keVIR cameraResolution0.6 nm @ 30 kV (STEM) 0.6 nm @ 15-2 kVIntegrated Beam current measurement0.7 nm @ 1kVGIS	Column typeElstar UC(detected signals)Manipulator typeSource typeSchottky FEG with monochromatorTLD (SE, BSE)MovementsImaging modesfield freeMD (BSE)Sample StageImaging modesfield freeMD (BSE)X,YXHR immersionETD (SE, BSE)ZEDS optimizedFSD (BSE)RotationBeam decelerationCBS (BSE)TiltProbe current0.8 pA to 100 nASTEM (TE)Tilt accuracyLanding energy20 eV to 30 keVICE (SE, SI)Maximum Sample SIon OpticsTomahawkEBSD EDAX Hikari XPMax. thickness (loadlock)Source typeGa LMISEDS EDAX SDD Octane Super 60 mm²Max. thickness via chamber doorProbe current0.1 pA to 65 nAOthersStage typeResolution0.6 nm @ 30 kV (STEM) 0.6 nm @ 15-2 kVIntegrated Beam current measurementAccessories0.7 nm @ 1kVGISCryo cleaner

4 nm @ 30 kV

→ MORE INFO

detector (bottom)

(top) and imaged using STEM

Guarantor: Ondřej Man (ondrej.man@ceitec.vutbr.cz) Web: http://nano.ceitec.cz/focused-ion-beam-scanning-electron-microscope-fei-helios-nanolab-660-helios/

l beam





tungsten



Additional cold trap (part of CryoMAT)

SPECIFICATIONS